

MTP20N15E

Preferred Device

Power MOSFET 20 Amps, 150 Volts N-Channel TO-220

This Power MOSFET is designed to withstand high energy in the avalanche and commutation modes. The energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for low voltage, high speed switching applications in power converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional safety margin against unexpected voltage transients.

- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	150	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0\text{ M}\Omega$)	V_{DGR}	150	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GSM}	± 32	
– Non-Repetitive ($t_p \leq 10\text{ ms}$)			
Drain – Continuous	I_D	20	Adc
– Continuous @ 100°C	I_D	12	
– Single Pulse ($t_p \leq 10\text{ }\mu\text{s}$)	I_{DM}	60	
Total Power Dissipation	P_D	112	Watts
Derate above 25°C		0.9	$\text{W}/^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$
Single Drain-to-Source Avalanche Energy	E_{AS}	60	mJ
– Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 120\text{ Vdc}$, $V_{GS} = 10\text{ Vdc}$, $I_L = 20\text{ Apk}$, $L = 0.3\text{ mH}$)			
Thermal Resistance	$R_{\theta JC}$	1.1	$^\circ\text{C}/\text{W}$
– Junction to Case	$R_{\theta JA}$	62.5	
– Junction to Ambient			
Maximum Lead Temperature for Soldering Purposes, $1/8''$ from case for 10 seconds	T_L	260	$^\circ\text{C}$



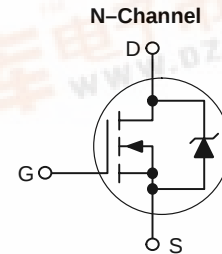
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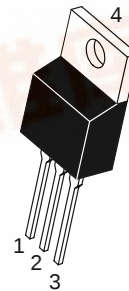
20 AMPERES

150 VOLTS

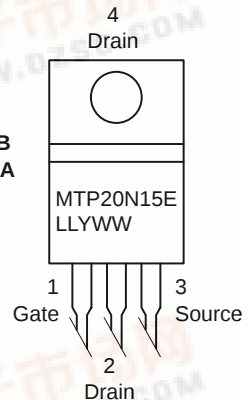
$R_{DS(on)} = 130\text{ m}\Omega$



MARKING DIAGRAM & PIN ASSIGNMENT



TO-220AB
CASE 221A
STYLE 5



MTP20N15E = Device Code
LL = Location Code
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MTP20N15E	TO-220AB	50 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

MTP20N15E

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 0.25 mAdc) Temperature Coefficient (Positive)	V _(BR) DSS	150 –	– TBD	– –	Vdc mV/°C
Zero Gate Voltage Collector Current (V _{DS} = 150 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 150 Vdc, V _{GS} = 0 Vdc, T _J = 125°C)	I _{DSS}	– –	– –	10 100	μAdc
Gate–Body Leakage Current (V _{GS} = ± 20 Vdc, V _{DS} = 0)	I _{GSS(f)} I _{GSS(r)}	– –	– –	100 100	nAdc

ON CHARACTERISTICS (Note 1.)

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 0.25 mAdc) Temperature Coefficient (Negative)	V _{GS(th)}	2.0 –	– TBD	4.0 –	Vdc mV/°C
Static Drain–Source On–Resistance (V _{GS} = 10 Vdc, I _D = 10 Adc)	R _{DS(on)}	–	0.12	0.13	Ohm
Drain–Source On–Voltage (V _{GS} = 10 Vdc) (I _D = 20 Adc) (I _D = 10 Adc, T _J = 125°C)	V _{DS(on)}	– –	– –	2.8 2.6	Vdc
Forward Transconductance (V _{DS} = 13 Vdc, I _D = 10 Adc)	g _{FS}	8.0	11	–	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	–	1133	1627	pF
Output Capacitance		C _{oss}	–	332	474	
Transfer Capacitance		C _{rss}	–	105	174	

SWITCHING CHARACTERISTICS (Note 2.)

Turn–On Delay Time	(V _{DD} = 75 Vdc, I _D = 20 Adc, V _{GS} = 10 Vdc, R _G = 9.1 Ω)	t _{d(on)}	–	11	25	ns
Rise Time		t _r	–	77	153	
Turn–Off Delay Time		t _{d(off)}	–	33	67	
Fall Time		t _f	–	49	97	
Gate Charge	(V _{DS} = 120 Vdc, I _D = 20 Adc, V _{GS} = 10 Vdc)	Q _T	–	39.1	55.9	nC
		Q ₁	–	7.5	–	
		Q ₂	–	22	–	
		Q ₃	–	17	–	

SOURCE–DRAIN DIODE CHARACTERISTICS

Forward On–Voltage (Note 1.)	(I _S = 20 Adc, V _{GS} = 0 Vdc) (I _S = 20 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	– –	– –	1.5 –	Vdc
Reverse Recovery Time	(I _S = 20 Adc, V _{GS} = 0 Vdc, di _S /dt = 100 A/μs)	t _{rr}	–	160	–	ns
		t _a	–	123	–	
		t _b	–	36.5	–	
Reverse Recovery Stored Charge		Q _{RR}	–	1.1	–	μC

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

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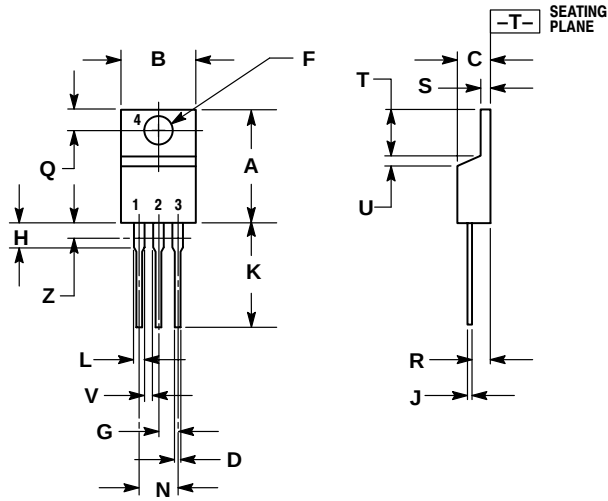
PACKAGE DIMENSIONS

TO-220 THREE-LEAD

TO-220AB

CASE 221A-09

ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 5:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

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ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 303-675-2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

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